

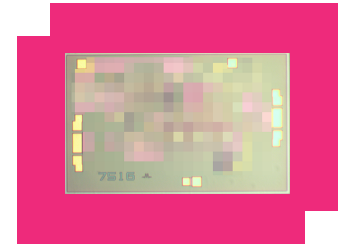
# APM-7516CH

## 1 GHz – 22 GHz Low Phase Noise Amplifier

### DEVICE OVERVIEW

#### General Description

The APM-7516 is a robust broadband distributed, low phase noise LO driver amplifier designed to provide greater than +20 dBm output power with excellent return losses and high input power handling. This amplifier uses GaAs HBT technology for low phase noise and is optimized to provide enough power to drive the LO port of an S-diode mixer from 1 GHz to 18 GHz or of an H or L diode mixer from 1 GHz to 22 GHz. This amplifier can be operated with a variety of bias conditions for both low power and high-power applications.



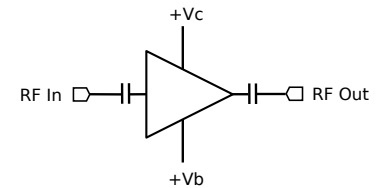
#### Features

- -164 dBc/Hz phase noise at 10 kHz offset frequency
- +20 dBm output power up to 18GHz
- High Linearity (+33 dBm OIP3)
- Excellent Return Losses
- +20dBm Input Power Handling
- Positive-only biasing

#### Applications

- Mobile test and measurement equipment
- 5G transceivers
- Driver amplifier L,H,S – diode mixers
- Radar
- SATCOM

#### Functional Block Diagram



#### Part Ordering Options

Part Number	Description	Package	Green Status	Product Lifecycle	Export Classification
APM-7516CH	1 GHz – 22 GHz Low Phase Noise Amplifier	CH	REACH RoHS	Released	EAR99
<u>APM-7516KGD</u>	Known Good Die, 1 GHz – 22 GHz Low Phase Noise Amplifier	CH	REACH RoHS	Released	EAR99

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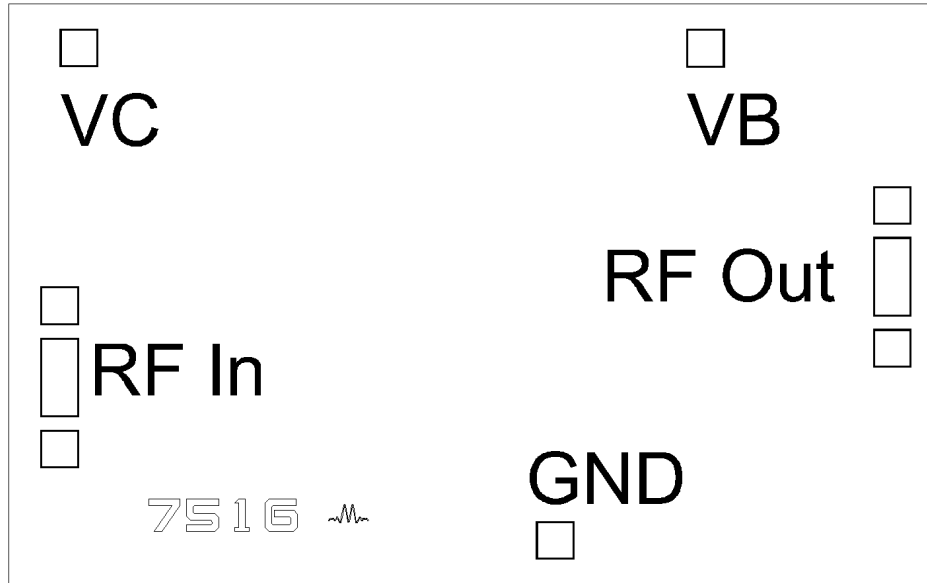
### Revision History

Revision Code	Revision Date	Comment
-	2025-07-25	Initial Release
A	2026-02-13	MTTF Table Added.

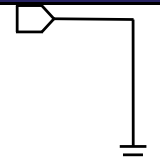
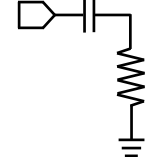
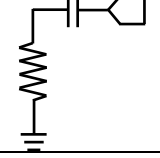
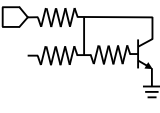
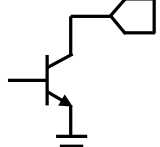
### Port Configuration and Functions

#### Port Diagram

A port diagram of the APM-7516CH is shown below.



#### Port Functions

Port	Function	Description	DC Equivalent Circuit
GND	Ground	Housing or outside of the coaxial cables must be connected to a DC/RF ground potential with high thermal and electrical conductivity.	
RF In	RF Input	This is the RF Input port of the amplifier die. It is RF matched to 50 Ω, and has built-in DC blocking capacitors.	
RF Out	RF Output	This is the amplifier's RF Output. It is RF matched to 50 Ω and has built-in DC blocking capacitors. Must have less than 7:1 VSWR when operating.	
VB	Base Current Mirror Bias Port	Port VB is the DC voltage bias for the current mirror that controls collector current supplied to the amplifier. Larger voltages result in a higher current draw through port VC, effectively functioning as a gain control pin of the amplifier. See Typical Performance Plots for performance at different bias conditions.	
VC	Collector DC Supply Port	Port VC is the DC voltage supply that supplies the amplifier's collector current. It is connected directly to the VC port on the amplifier IC.	

## Specifications

### Absolute Maximum Ratings

The Absolute Maximum Ratings indicate limits beyond which damage may occur to the device. If these limits are exceeded, the device may become inoperable or have a reduced lifetime.

Parameter	Maximum Rating	Unit
Collector Positive Bias Voltage (Vc)	6	V
Continuous Power Dissipation (PDISS) (at 85 °C case temp.)	1.2	W
Maximum Operating Temperature	85	°C
Maximum Storage Temperature	150	°C
Max Junction Temperature for MTTF > 1E6 hours	125	°C
Minimum Operating Temperature	-40	°C
Minimum Storage Temperature	-65	°C
Output Load VSWR	7	-
Positive Bias Current (Ic)	240	mA
Positive DC Current Mirror Current (Ib)	15	mA
Positive DC Current Mirror Voltage (Vb)	6	V
RF Input Power	20	dBm
$\theta_{JC}$ , Junction to Ambient Thermal Resistance	33	°C/W

### FIT and MTTF Table

T (°C)	$\lambda$ (TIF)	MTTF (hr)	MTTF (yr)
105	2,441.45	4.10E+05	47
85	310.48	3.22E+06	368
55	8.79	1.14E+08	12,992
25	0.12	8.24E+09	941,063

### Package Information

Parameter	Details	Rating
Dimensions	-	28.5 x 15 mm

### Recommended Operating Conditions

The Recommended Operating Conditions indicate the limits, inside which the device should be operated, to guarantee the performance given in Electrical Specifications. Operating outside these limits may not necessarily cause damage to the device, but the performance may degrade outside the limits of the electrical specifications. For limits, above which damage may occur, see Absolute Maximum Ratings.

Parameter	Min	Nominal	Max	Unit
Positive DC Current Mirror Current (Ib) <sup>1</sup>	-	5	-	mA
Positive DC Voltage (VC)	-	5	-	V
Positive DC Current Mirror Voltage (VB)	-	5	-	V
Positive DC Current (Ic) <sup>2</sup>	-	106	-	mA

[1][2] Recommended operating current conditions given without RF input applied. Please see typical performance plots for relationship between RF input power and DC current draw.

### Sequencing Requirements

There is no sequencing required to power up or power down the amplifier. Amplifier must have an output load connected when operating.

**Electrical Specifications**

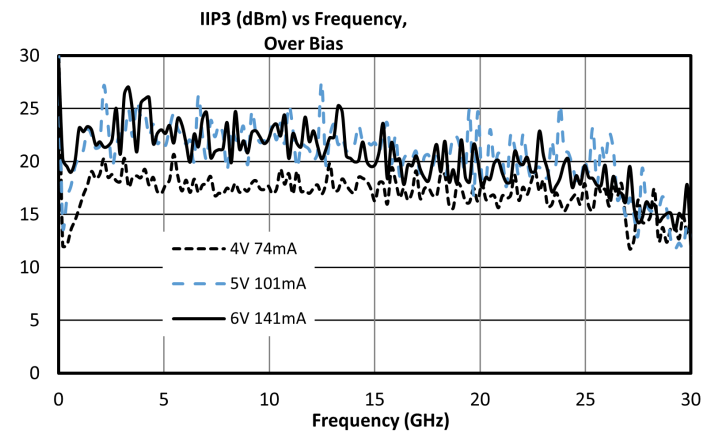
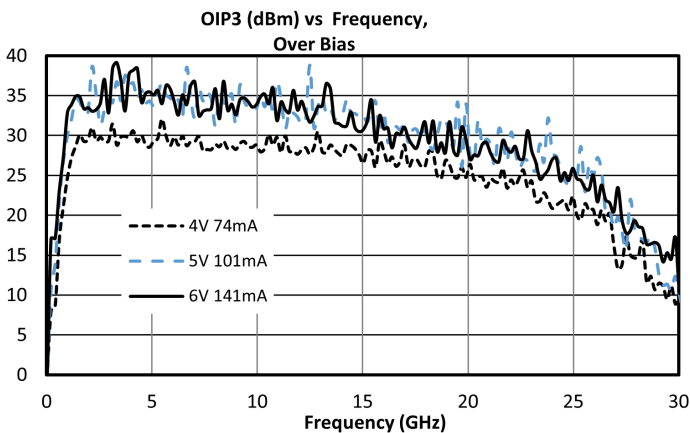
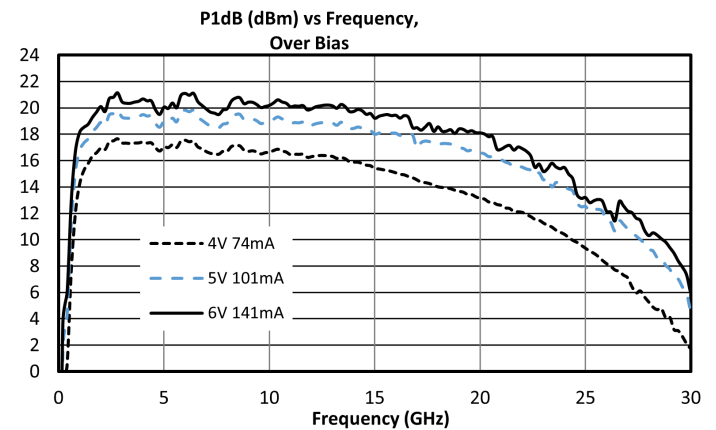
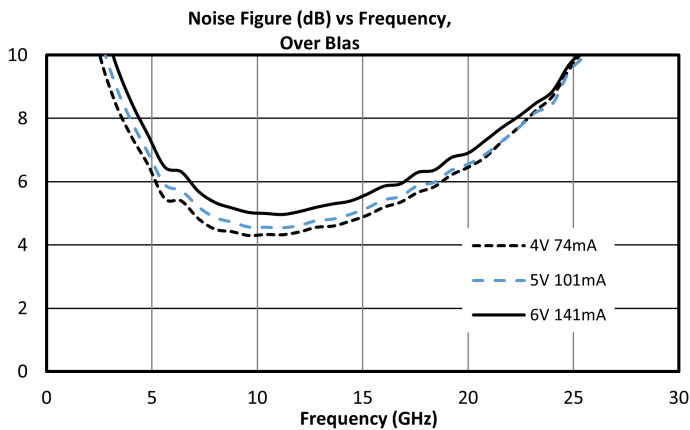
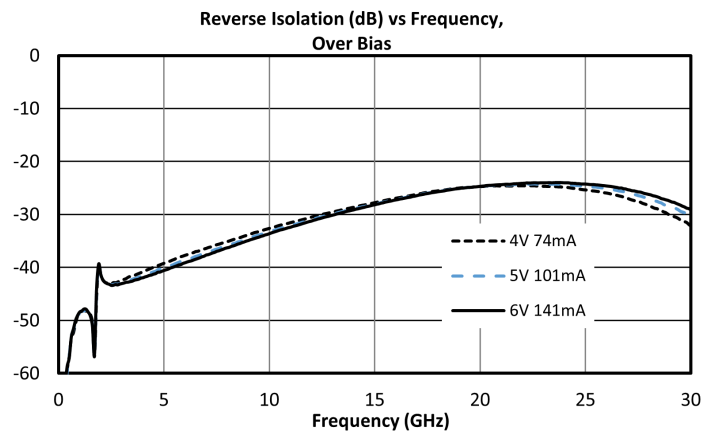
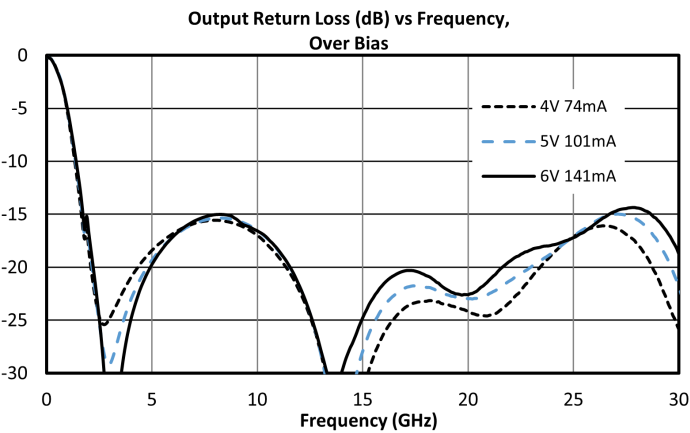
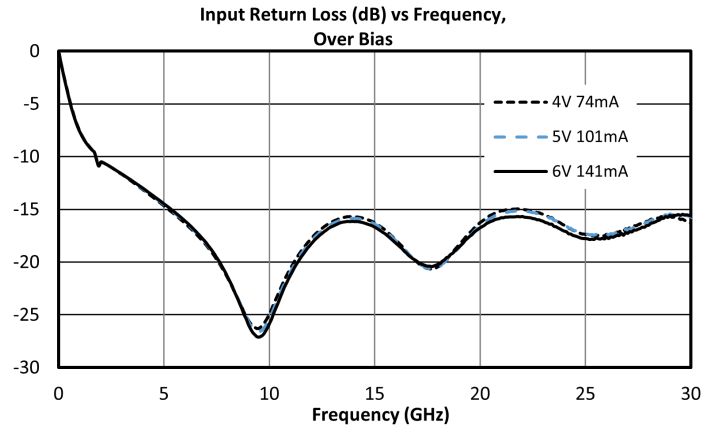
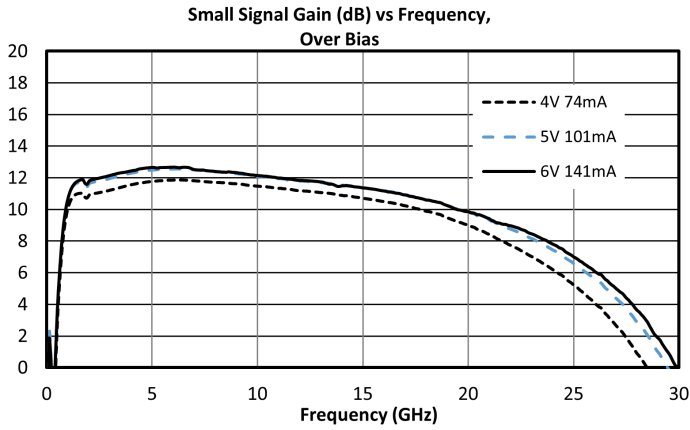
The electrical specifications apply at TA=+25°C in a 50Ω system. Min and Max limits apply only to our connectorized units and are guaranteed at TA=+25°C.

Parameter	Test Conditions	Minimum Frequency (GHz)	Maximum Frequency (GHz)	Min	Typ	Max	Unit
Small Signal Gain	5V/5V bias, -15 dBm Input Power	1	22	-	12	-	dB
Saturated Output Power	5V/5V bias, P5dB	1	3	-	23	-	dBm
Saturated Output Power	5V/5V bias, P5dB	3	15	19	23	-	dBm
Saturated Output Power	5V/5V bias, P5dB	15	22	-	20	-	dBm
Current Consumption	5V/4V	-	-	-	74	-	mA
Current Consumption	5V/5V	-	-	-	106	-	mA
Current Consumption	5V/6V	-	-	-	141	-	mA
Current Mirror, Ib	5V/4V	-	-	-	4	-	mA
Current Mirror, Ib	5V/5V	-	-	-	5	-	mA
Current Mirror, Ib	5V/6V	-	-	-	7	-	mA
Input IP3	5V/5V, -15 dBm Input Power	1	22	-	21	-	dBm
Input Power for Saturation	5V/5V	1	22	-	12	-	dBm
Input Return Loss	5V/5V bias, -15 dBm Input Power	1	22	-	18	-	dB
Noise Figure	5V/5V bias, -30 dBm Input Power	1	22	-	6	-	dB
Output IP3	5V/5V, -15 dBm Input Power	1	22	-	33	-	dBm
Output P1dB	5V/5V	1	22	-	18	-	dBm
Output Return Loss	5V/5V bias, -15 dBm Input Power	1	22	-	20	-	dB
Phase Noise @ 10 kHz Offset	+13 dBm Input power	4	4	-	-164	-	dBc/Hz
Reverse Isolation	5V/5V bias, -15 dBm Input Power	1	22	-	34	-	dB

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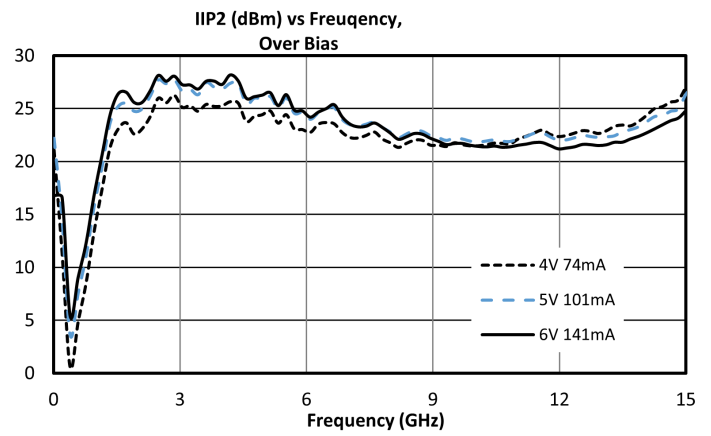
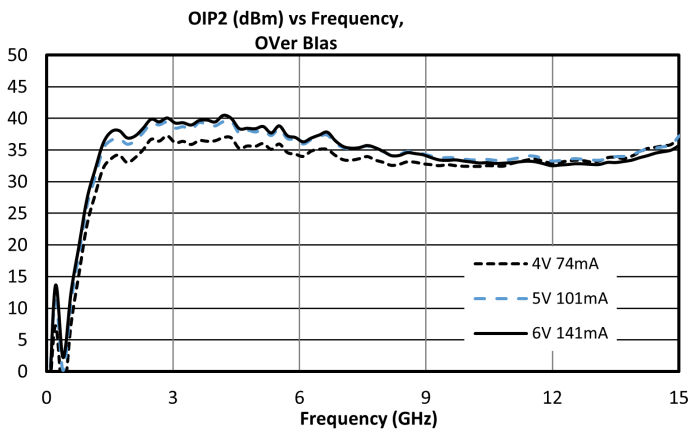
## 1 GHz – 22 GHz Low Phase Noise Amplifier

### APM-7516CH Typical Performance Plots



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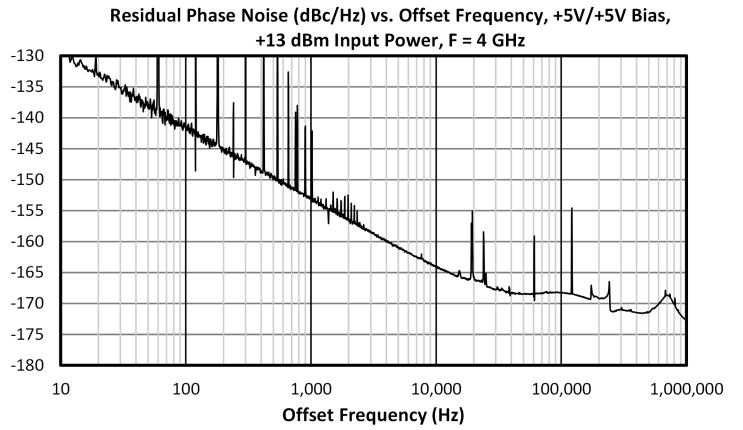
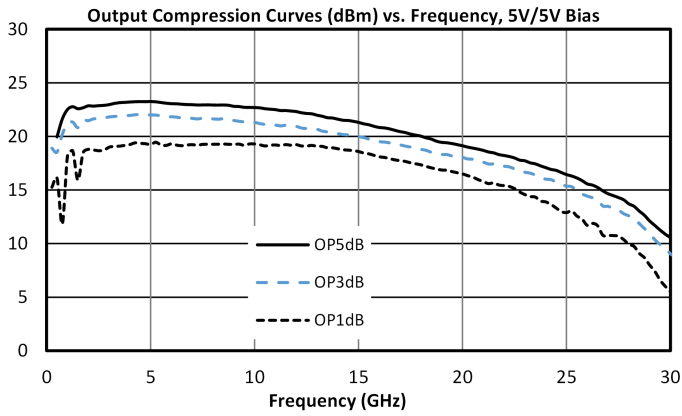
## 1 GHz – 22 GHz Low Phase Noise Amplifier



# APM-7516CH

1 GHz – 22 GHz Low Phase Noise Amplifier

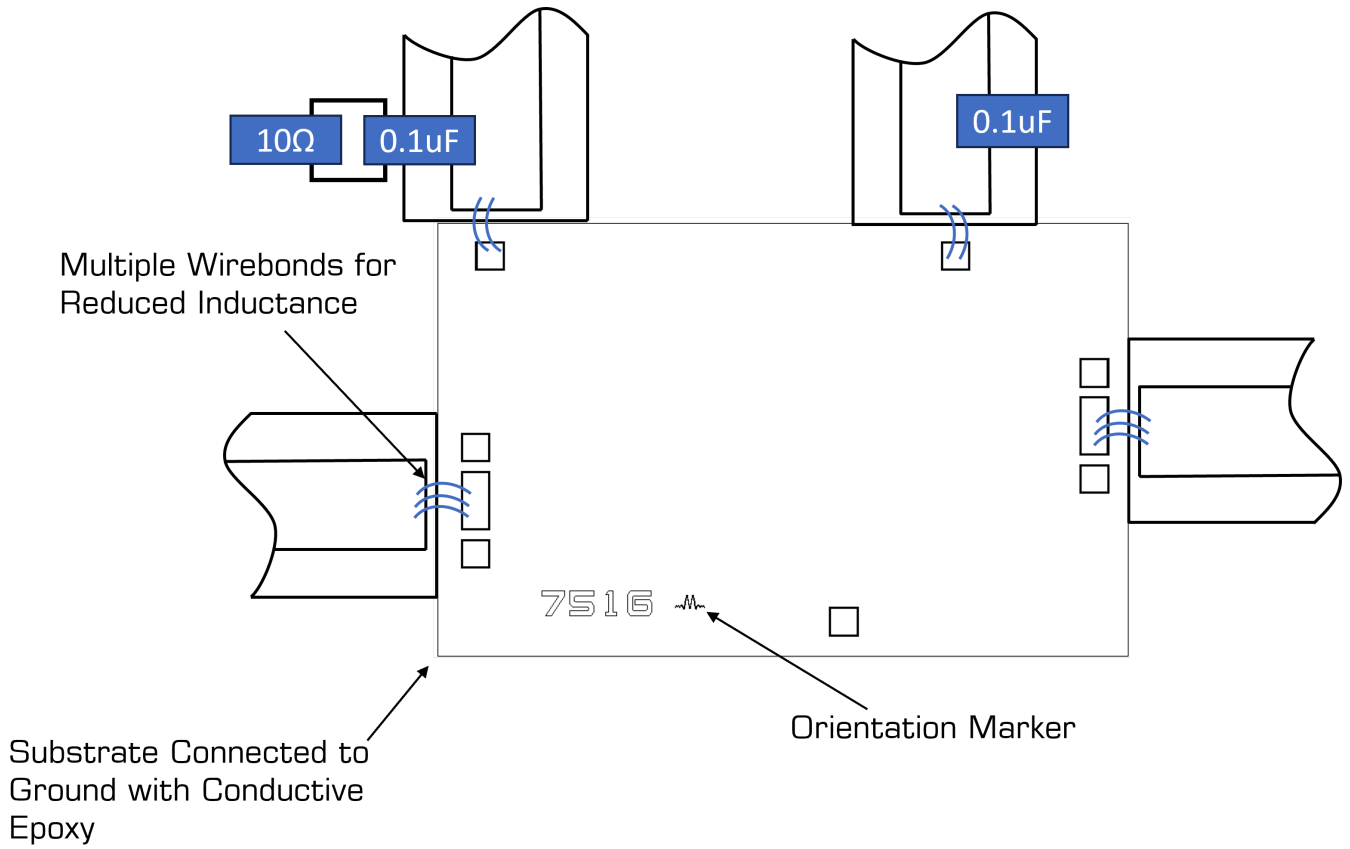
## APM-7516PA Typical Performance Plots



### **Application Information**

Below is the recommended application circuit for the APM-7516CH.

**Application Circuit**



**Application Circuit Description**

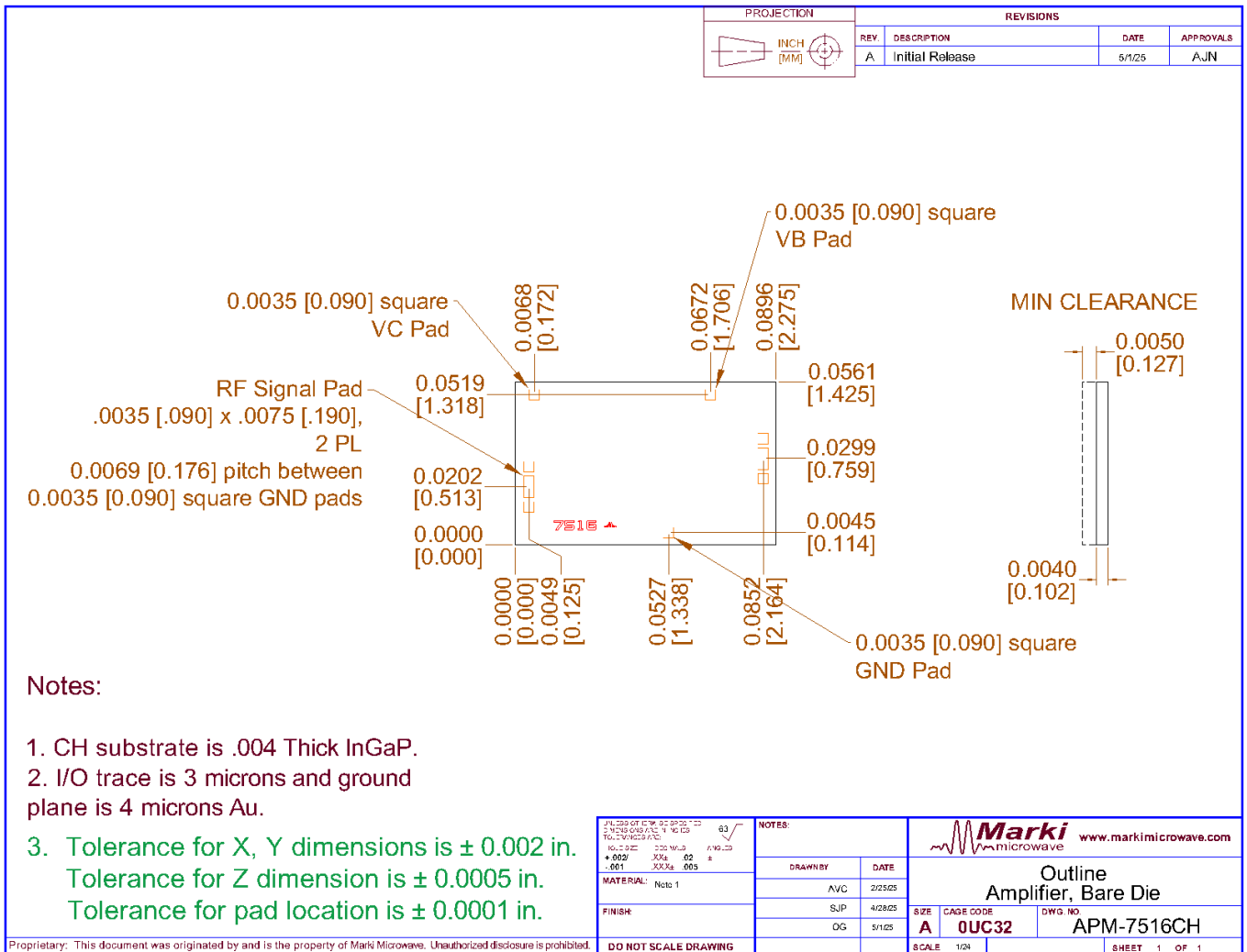
RF input and output should be soldered to 50 Ω traces.

Description	Sample Part Number
0402 Capacitor .1uF 16V	Kyocera 0402YG104ZAT2A
0402 Resistor 10 Ohm	Vishay Dale CRCW040210R0FKED

### Mechanical Data

### Outline Drawing

Download : [Outline 2D Drawing](#)



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